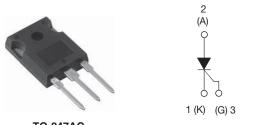


Thyristor High Voltage, Phase Control SCR, 40 A



TO-247AC

PRODUCT SUMMARY	PRODUCT SUMMARY								
Package	TO-247AC								
Diode variation	Single SCR								
I _{T(AV)}	35 A								
V _{DRM} /V _{RRM}	800 V, 1200 V								
V _{TM}	1.45 V								
I _{GT}	150 mA								
TJ	-40 °C to +125 °C								

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- Low IGT parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

DESCRIPTION

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	35	A						
I _{RMS}		55	~						
V _{RRM} /V _{DRM}		800/1200	V						
I _{TSM}		600	А						
V _T	40 A, T _J = 25 °C	1.45	V						
dV/dt		1000	V/µs						
dl/dt		100	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS										
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA							
VS-40TPS08APbF, VS-40TPS08A-M3	800	900								
VS-40TPS08PbF, VS-40TPS08-M3	800	900	10							
VS-40TPS12APbF, VS-40TPS12A-M3	1200	1300	10							
VS-40TPS12PbF, VS-40TPS12-M3	1200	1300								

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ABSOLUTE MAXIMUM RATINGS	;					
PARAMETER	SYMBOL	т	EST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 79 °C, 180° co	nduction half sine wave	e	35	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}				55	А
Maximum peak, one-cycle	I _{TSM}	10 ms sine pulse, ra	10 ms sine pulse, rated V _{RRM} applied			
non-repetitive surge current	ISM	10 ms sine pulse, no	1-11-1	600		
Maximum I ² t for fusing	l ² t	10 ms sine pulse, ra	ted V _{RRM} applied	Initial $T_{1} = T_{1} max.$	1250	A ² s
Maximum tior fusing	11	10 ms sine pulse, no	o voltage reapplied		1760	A-S
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms,	17 600	A²√s		
Low level value of threshold voltage	V _{T(TO)1}		1.02	v		
High level value of threshold voltage	V _{T(TO)2}	Т., = 125 °С	1.23			
Low level value of on-state slope resistance	r _{t1}	1j = 125 C	9.74	mΩ		
High level value of on-state slope resistance	r _{t2}		7.50			
Maximum peak on-state voltage	V _{TM}	110 A, T _J = 25 °C			1.85	V
Maximum rate of rise of turned-on current	dl/dt	T _J = 25 °C			100	A/µs
Maximum holding current	I _H	Anode supply = 6 V,	resistive load, initial T_J	= 1 A, I _T = 25 °C	200	
Maximum latching current	١L	Anode supply = 6 V	, resistive load, $T_J = 25$	°C	300	
		T _J = 25 °C			0.5	mA
Maximum reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{D}$	RM	10	
Maximum rate of rise of off-state voltage 40TPS12A	dV/dt				500	V/µs
Maximum rate of rise of off-state voltage 40TPS12	uv/ui	ij = ij maximum, ili	T_{J} = T_{J} maximum, linear to 80 % $V_{DRM},$ $R_{g}\text{-}$ k = 100 Ω			

TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			10	W
Maximum average gate power	P _{G(AV)}			2.5	vv
Maximum peak gate current	I _{GM}			2.5	А
Maximum peak negative gate voltage	- V _{GM}			10	V
		T _J = - 40 °C		4.0	
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	2.5	V
		T _J = 125 °C		1.7	
		T _J = - 40 °C		270	mA
	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	
Maximum required DC gate current to trigger		T _J = 125 °C		80	
		$T_J = 25 \ ^{\circ}C$, for 40TPS08AP	40		
Maximum DC gate voltage not to trigger for 40TPS12	V _{GD}	T 105 °C V Deted	velue	0.25	V
Maximum DC gate current not to trigger for 40TPS12	I _{GD}	T _J = 125 °C, V _{DRM} = Rated	6	mA	
Maximum DC gate voltage not to trigger for 40TPS12A	V_{GD}	$T = 125 \circ C V = -$ Botod	0.15	V	
Maximum DC gate current not to trigger for 40TPS12A	I _{GD}	T _J = 125 °C, V _{DRM} = Rated	value	1	mA

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and sto temperature range	rage	T _J , T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case		R _{thJC}							
Maximum thermal resistance, junction to ambient		R _{thJA}	DC operation	40	°C/W				
Maximum thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.2					
Approximate weight				6	g				
Approximate weight				0.21	oz.				
	minimum			6 (5)	kgf ⋅ cm				
Mounting torque	maximum			12 (10)	(lbf · in)				
				40TP	S08A				
				40TP	S12A				
Marking device			Case style TO-247AC	40TF	PS08				
				40TF	PS12				

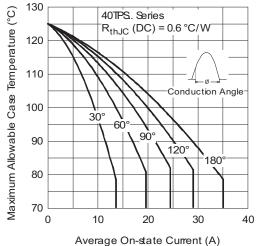
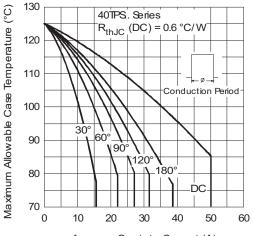
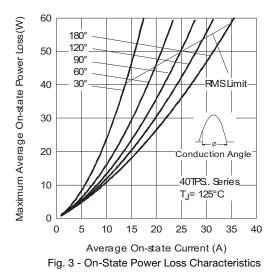


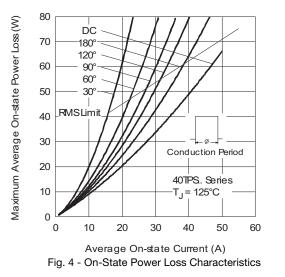
Fig. 1 - Current Rating Characteristics



Average On-state Current (A) Fig. 2 - Current Rating Characteristics







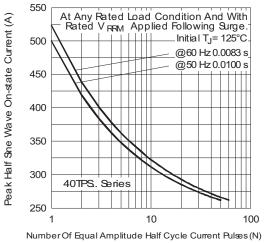
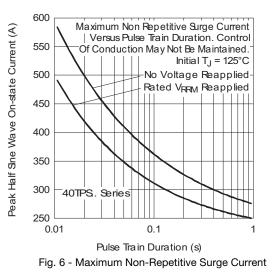
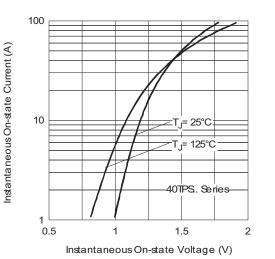
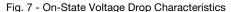


Fig. 5 - Maximum Non-Repetitive Surge Current







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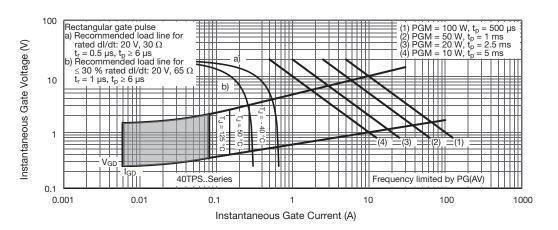


Fig. 8 - Gate Characteristics

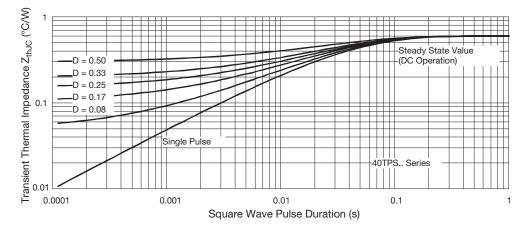


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code	VS-	40	т	Р	S	12	A	PbF
	1	2	3	4	5	6	7	8
	1 -	- Visł	nay Sem	niconduc	tors pro	duct		
	2 -	Cur	rent rati	ng (40 =	40 A)			
	3 -	Circ	uit confi	iguratior	n:			
		T =	Thyristo	or				
	4 -	Pac	kage:					
	_	P =	TO-247					
	5 -		e of silic					
					ery recti	fier		08 =
	6 -	Volt	age rati	ngs —				12 = 1
	7 -	• A	= Low I	gt selec	tion 40 r	mA max	timum	
	_	• N	one = S	tandard	lgt sele	ction		
	8 -	Env	ironmer	ntal digit				
		PbF	= Lead	l (Pb)-fre	ee and F	RoHS co	omplian	t
		-M3	= Halor	non_froo	RoHS	complia	nt and	torming

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORM	ATION (Example)		
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-40TPS08APbF	25	500	Antistatic plastic tubes
VS-40TPS08A-M3	25	500	Antistatic plastic tubes
VS-40TPS08PbF	25	500	Antistatic plastic tubes
VS-40TPS08-M3	25	500	Antistatic plastic tubes
VS-40TPS12APbF	25	500	Antistatic plastic tubes
VS-40TPS12A-M3	25	500	Antistatic plastic tubes
VS-40TPS12PbF	25	500	Antistatic plastic tubes
VS-40TPS12-M3	25	500	Antistatic plastic tubes

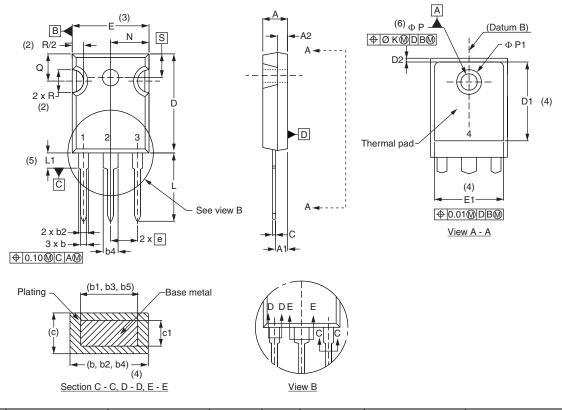
LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95542					
Part marking information	TO-247AC PbF	www.vishay.com/doc?95226					
	TO-247AC-M3	www.vishay.com/doc?95007					





TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			Ш	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØР	3.56	3.66	0.14	0.144	
с	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension c and Q

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